

Single N-Channel, 20V, 1.85A, Power MOSFET

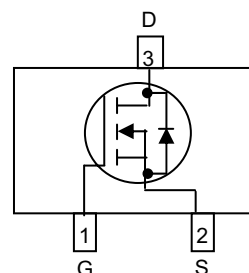
V _{DS} (V)	R _{ds(on)} (Ω)	I _D (A)
20	0.072@ V _{GS} =4.5V	1.8
	0.088@ V _{GS} =2.5V	1.5
	0.115@ V _{GS} =1.8V	1.0



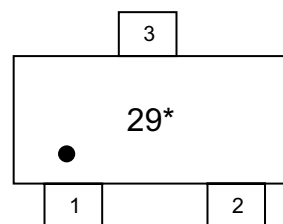
Descriptions

The WNM2029 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent R_{DS (ON)} with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WNM2029 is Pb-free.

SOT-323



Pin configuration (Top view)



29 = Device Code
 * = Month (A~Z)

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- Extremely Low Threshold Voltage
- Small package SOT-323

Marking

Applications

- Driver for Relay, Solenoid, Motor, LED etc.
- DC-DC converter circuit
- Power Switch
- Load Switch
- Charging

Order information

Device	Package	Shipping
WNM2029-3/TR	SOT-323	3000/Reel&Tape

Absolute Maximum ratings

Parameter		Symbol	10 S	Steady State	Unit
Drain-Source Voltage		V_{DS}	20		V
Gate-Source Voltage		V_{GS}	± 12		
Continuous Drain Current ^a	$T_A=25^\circ\text{C}$	I_D	1.85	1.69	A
	$T_A=70^\circ\text{C}$		1.48	1.35	
Maximum Power Dissipation ^a	$T_A=25^\circ\text{C}$	P_D	0.36	0.3	W
	$T_A=70^\circ\text{C}$		0.23	0.19	
Continuous Drain Current ^b	$T_A=25^\circ\text{C}$	I_D	1.65	1.51	A
	$T_A=70^\circ\text{C}$		1.32	1.21	
Maximum Power Dissipation ^b	$T_A=25^\circ\text{C}$	P_D	0.28	0.24	W
	$T_A=70^\circ\text{C}$		0.18	0.15	
Pulsed Drain Current ^c		I_{DM}	8		A
Operating Junction Temperature		T_J	150		$^\circ\text{C}$
Lead Temperature		T_L	260		$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150		$^\circ\text{C}$

Thermal resistance ratings

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance ^a	$t \leq 10 \text{ s}$	$R_{\theta JA}$	290	345	$^\circ\text{C/W}$
	Steady State		335	415	
Junction-to-Ambient Thermal Resistance ^b	$t \leq 10 \text{ s}$	$R_{\theta JA}$	380	435	
	Steady State		450	520	
Junction-to-Case Thermal Resistance		$R_{\theta JC}$	270	310	

a Surface mounted on FR4 Board using 1 square inch pad size, 1oz copper

b Surface mounted on FR4 board using minimum pad size, 1oz copper

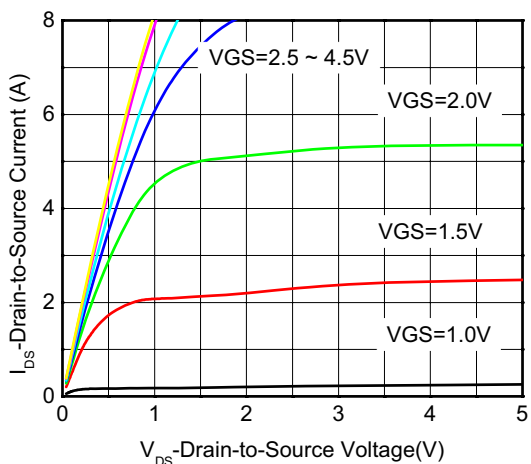
c Repetitive rating, pulse width limited by junction temperature, $t_p=10\mu\text{s}$, Duty Cycle=1%

d Repetitive rating, pulse width limited by junction temperature $T_J=150^\circ\text{C}$.

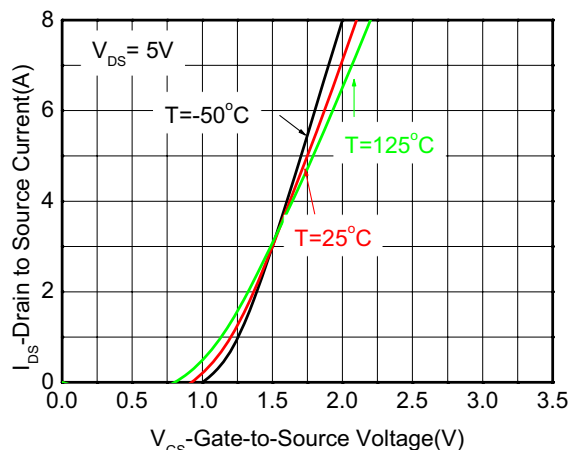
Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 250\mu\text{A}$	20.5			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 16\text{ V}, V_{GS} = 0\text{ V}$			100	nA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = 250\mu\text{A}$	0.50	0.65	0.80	V
Drain-to-source On-resistance	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 1.8\text{ A}$		72	87	mΩ
		$V_{GS} = 2.5\text{ V}, I_D = 1.5\text{ A}$		88	105	
		$V_{GS} = 1.8\text{ V}, I_D = 1.0\text{ A}$		115	138	
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{ V}, I_D = 1.8\text{ A}$		6		S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = 10\text{ V}$		185		pF
Output Capacitance	C_{OSS}			58		
Reverse Transfer Capacitance	C_{RSS}			54		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}, I_D = 1.8\text{ A}$		4.1		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.2		
Gate-to-Source Charge	Q_{GS}			0.6		
Gate-to-Drain Charge	Q_{GD}			1.25		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_d(ON)$	$V_{GS} = 4.5\text{ V}, V_{DS} = 6\text{ V}, R_L = 3\ \Omega, R_G = 6\ \Omega$		9.0		ns
Rise Time	t_r			14.0		
Turn-Off Delay Time	$t_d(OFF)$			25.0		
Fall Time	t_f			9.0		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = 1.0\text{ A}$	0.5	0.7	1.0	V

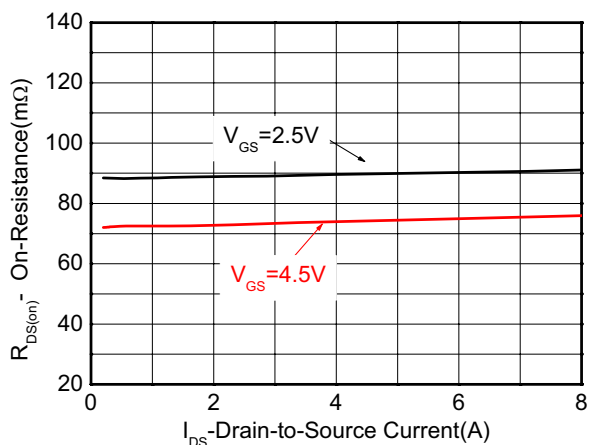
Typical Characteristics (Ta=25°C, unless otherwise noted)



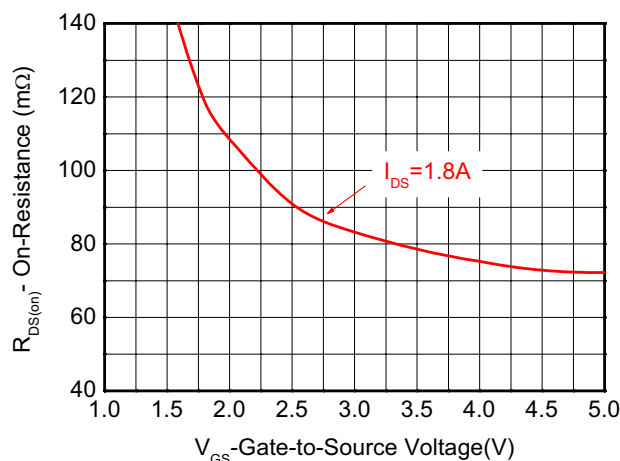
Output characteristics



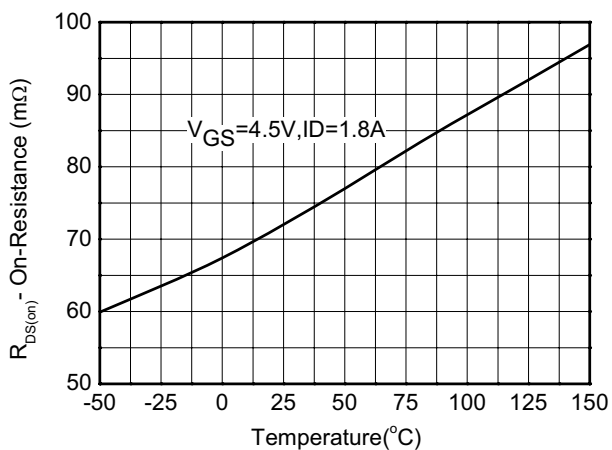
Transfer characteristics



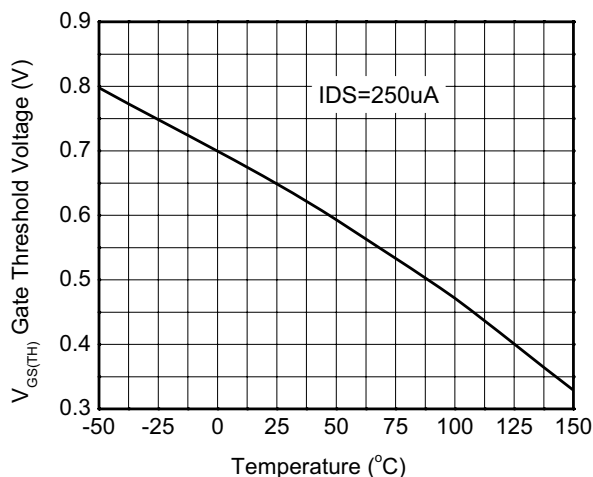
On-Resistance vs. Drain current



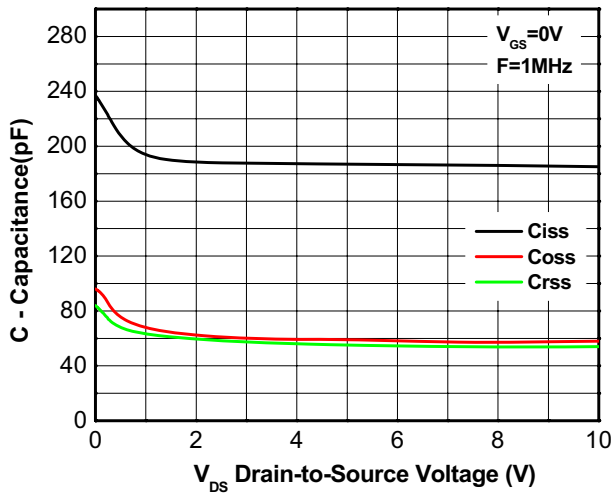
On-Resistance vs. Gate-to-Source voltage



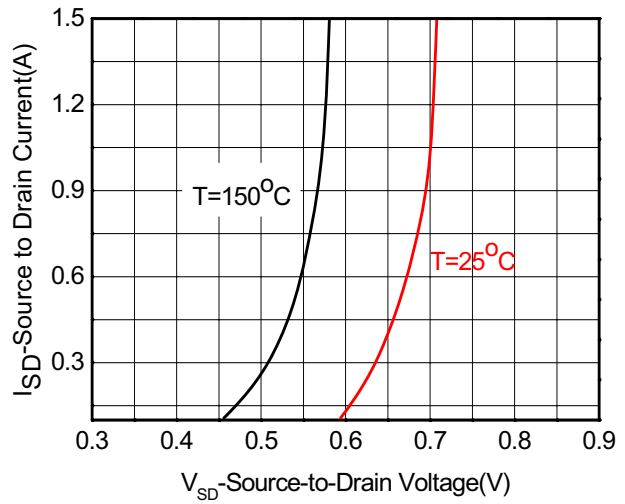
On-Resistance vs. Junction temperature



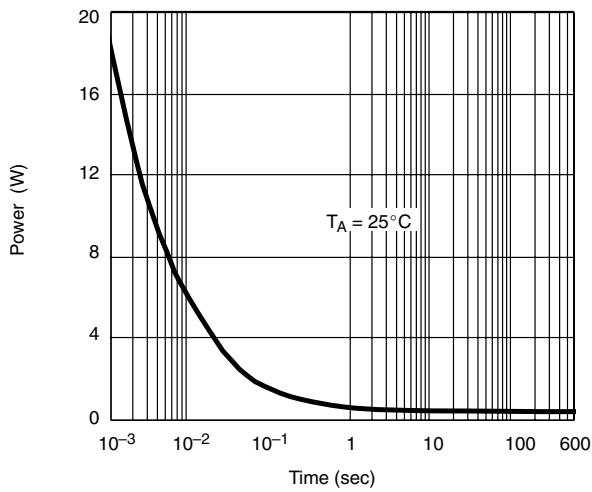
Threshold voltage vs. Temperature



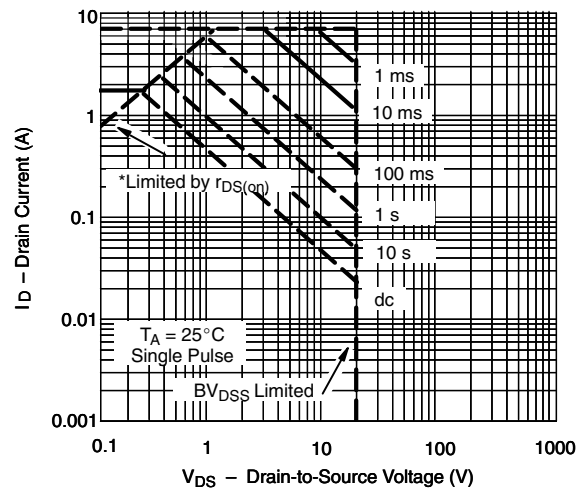
Capacitance



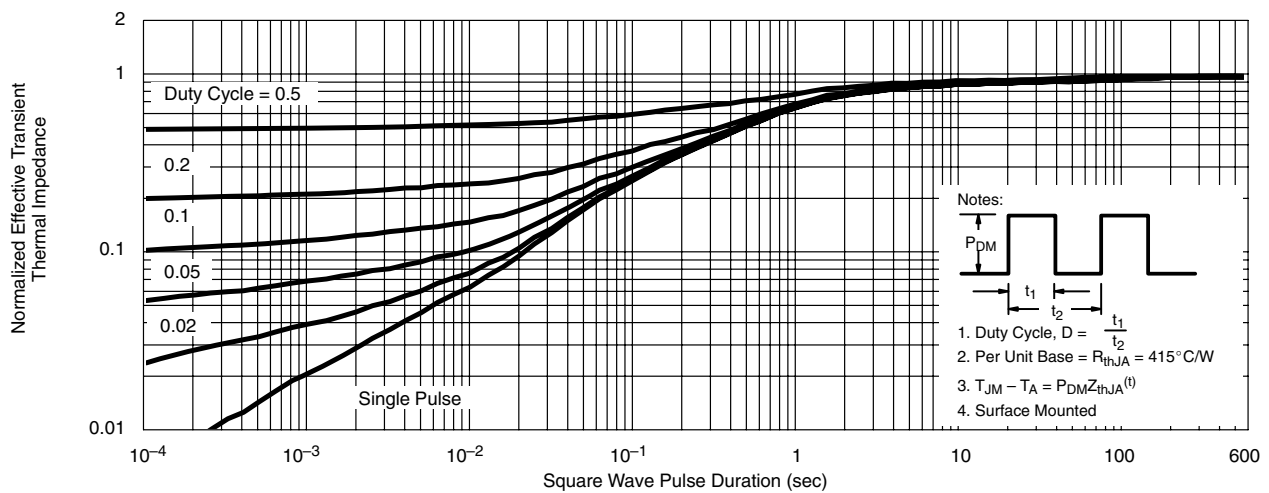
Body diode forward voltage



Single pulse power



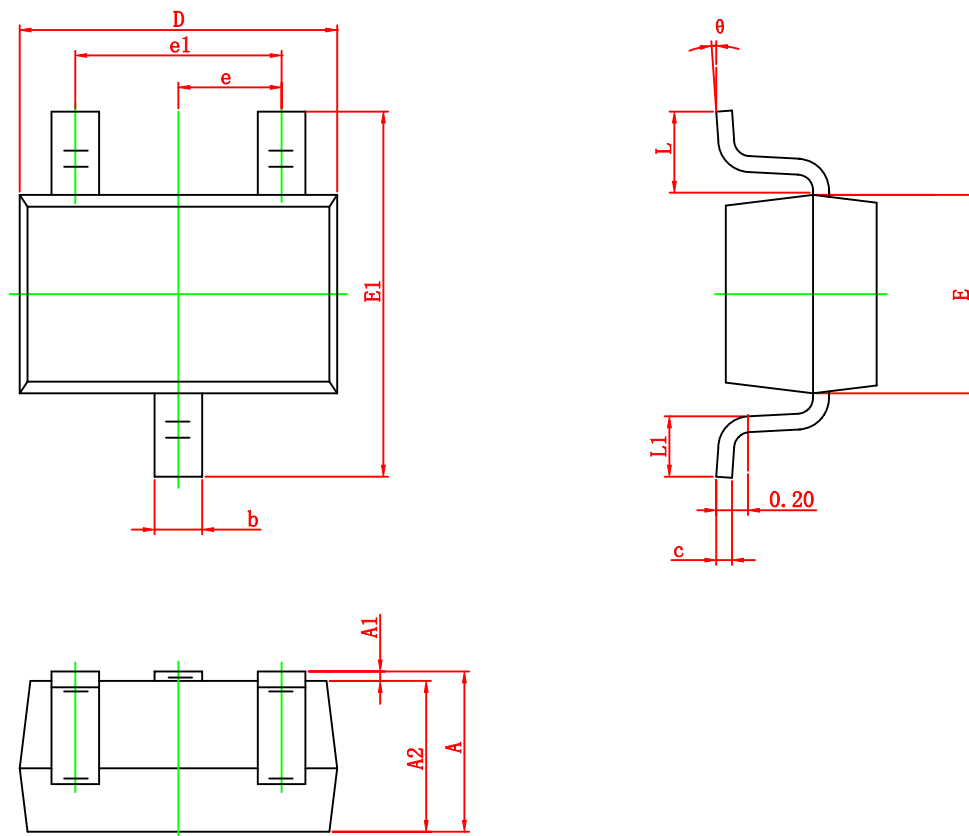
Safe operating power



Transient thermal response (Junction-to-Ambient)

Package outline dimensions

SOT-323



Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.900	1.000	1.100
A1	0.000	0.050	0.100
A2	0.900	0.950	1.000
b	0.200	0.300	0.400
c	0.080	0.115	0.150
D	2.000	2.100	2.200
E	1.150	1.250	1.350
E1	2.150	2.300	2.450
e	0.650TYP		
e1	1.200	1.300	1.400
L	0.525REF		
L1	0.260		0.460
θ	0°		8°